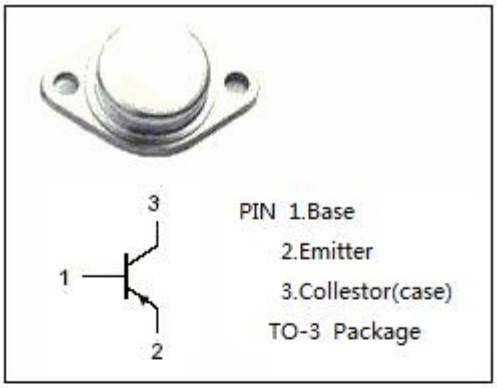
isc Silicon PNP Power Transistor 2N5884



DESCRIPTION

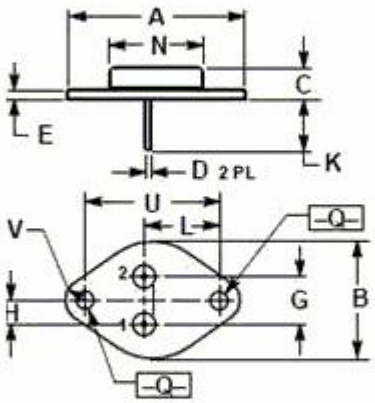
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$=-80V(Min)
- Minimum Lot-to-Lot variations for robust device Performance and reliable operation

APPLICATIONS

- Power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-25	A
I_B	Base Current-Continuous	-7.5	A
P_D	Collector Power Dissipation @ T_C=25℃	200	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -15.0A; I_B= -1.5A			-1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -25.0A; I_B= -6.25A			-4.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -25.0A; I_B= -6.25A			-2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -10A; V_{CE}= -4V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V; I_E= 0			-1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-1	mA
h_{FE-1}	DC Current Gain	I_C= -3A; V_{CE}= -4V	35			
h_{FE-2}	DC Current Gain	I_C= -10A; V_{CE}= -4V	20		100	
h_{FE-3}	DC Current Gain	I_C= -25A; V_{CE}= -4V	4			
fT	Trainsistion frequency	IC=-1A ; VCE=-10V;f=1MHz	4			MHz